



Product Overview

MBRA120ET3: Schottky Power Rectifier, Surface Mount, 1.0 A, 20 V

For complete documentation, see the data sheet

Product Description

The Schottky Rectifier employs the Schottky Barrier principle in a metal-to-silicon power rectifier. It features epitaxial construction with oxide passivation and metal overlay contact. It is ideally suited for low voltage, high frequency switching power supplies, free wheeling diodes and polarity protection diodes.

Features

- Compact Package with J-Bend Leads Ideal for Automated Handling
- Highly Stable Oxide Passivated Junction
- Guardring for Over-Voltage Protection
- Optimized for Low Leakage Current

Mechanical Characteristics:

- Case: Molded Epoxy
- Epoxy Meets UL94, VO at 1/8"
- Weight: 70 mg (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Polarity: Polarity Band Indicates Cathode Lead

Part Electrical Specifications

Product	Compliance	Status	Configuration	V_{RRM} Min (V)	V_F Max (V)	I_{RM} Max (uA)	$I_{O(rec)}$ Max (A)	I_{FSM} Max (A)	t_r Max (ns)	C, Max (pF)	Package Type
MBRA120ET3G	AEC Qualified Pb-free Halide free	Active	Single	20	0.53	10	1	40			SMA-2
NRVBA120ET3G	AEC Qualified PPAP Capable Pb-free Halide free	Active	Single	20	0.53	10	1	40			SMA-2

For more information please contact your local sales support at www.onsemi.com

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